

# 74HC244-Q100; 74HCT244-Q100

Octal buffer/line driver; 3-state

Rev. 1 — 7 August 2012

Product data sheet

## 1. General description

---

The 74HC244-Q100; 74HCT244-Q100 is an 8-bit buffer/line driver with 3-state outputs. The device can be used as two 4-bit buffers or one 8-bit buffer. The device features two output enables ( $1\overline{OE}$  and  $2\overline{OE}$ ), each controlling four of the 3-state outputs. A HIGH on  $n\overline{OE}$  causes the outputs to assume a high-impedance OFF-state. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of  $V_{CC}$ .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

## 2. Features and benefits

---

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - ◆ Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and from  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$
- Input levels:
  - ◆ For 74HC244-Q100: CMOS level
  - ◆ For 74HCT244-Q100: TTL level
- Octal bus interface
- Non-inverting 3-state outputs
- Multiple package options
- Complies with JEDEC standard no. 7 A
- ESD protection:
  - ◆ MIL-STD-883, method 3015 exceeds 2000 V
  - ◆ HBM JESD22-A114F exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V ( $C = 200\text{ pF}$ ,  $R = 0\ \Omega$ )



## 3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74HC244D-Q100 74HCT244D-Q100	-40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74HC244PW-Q100 74HCT244PW-Q100	-40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74HC244BQ-Q100 74HCT244BQ-Q100	-40 °C to +125 °C	DHVQFN20	plastic dual-in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 × 4.5 × 0.85 mm	SOT764-1

## 4. Functional diagram

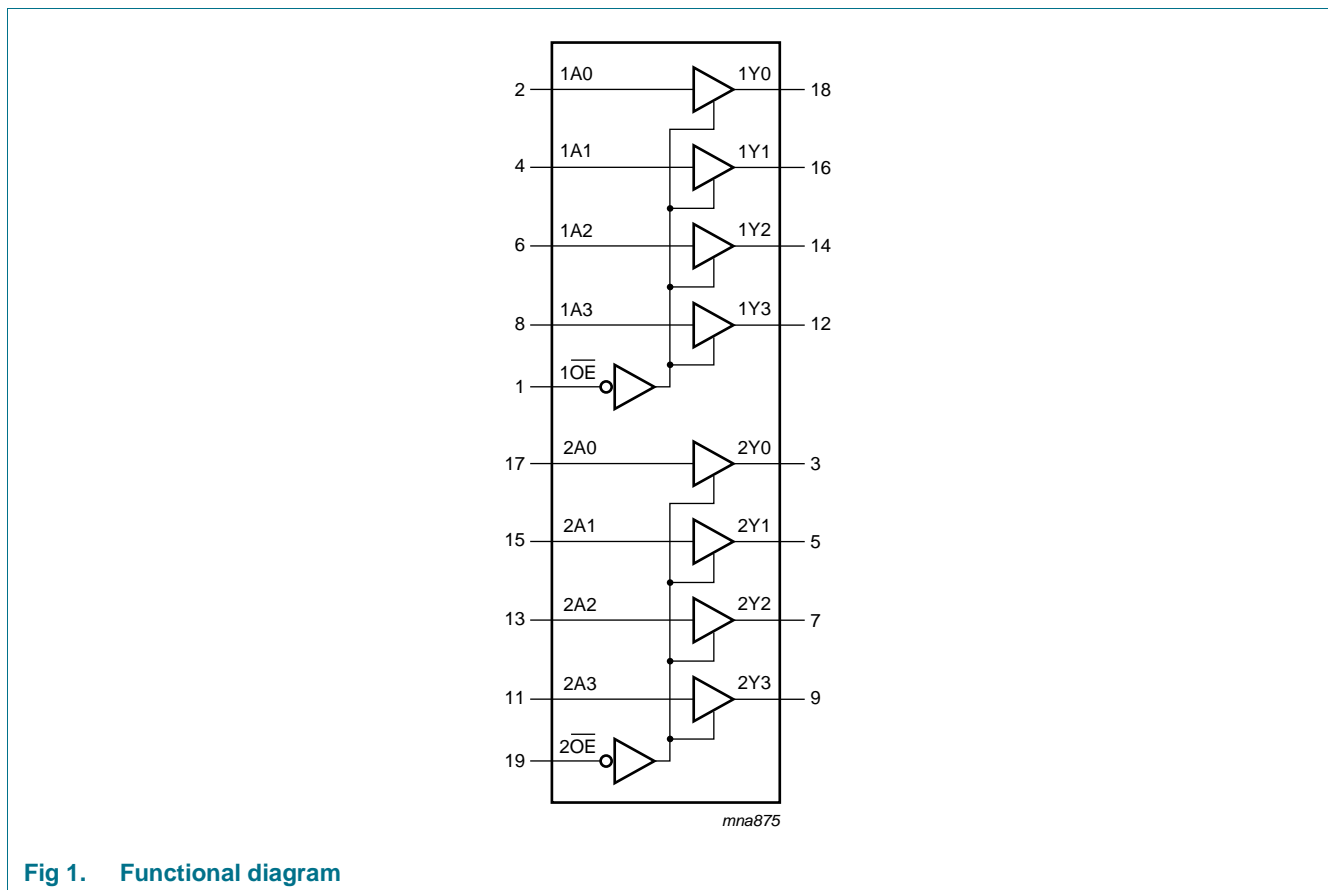


Fig 1. Functional diagram

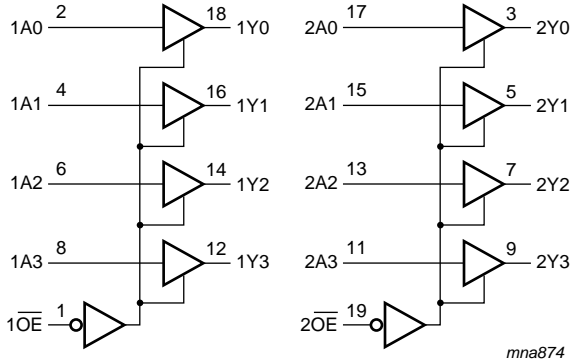


Fig 2. Logic symbol

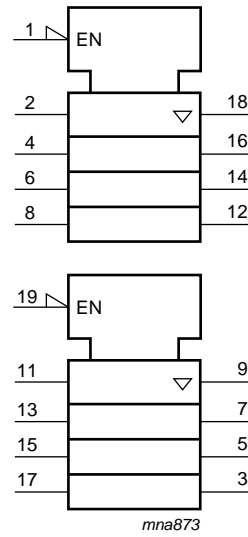


Fig 3. IEC symbol

## 5. Pinning information

### 5.1 Pinning

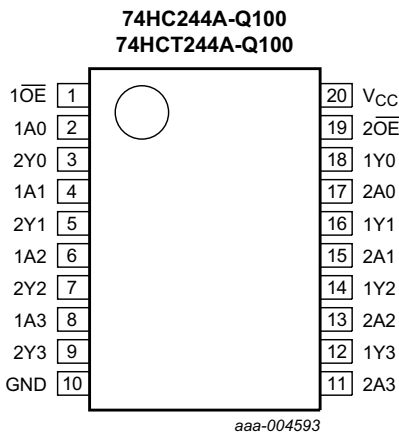
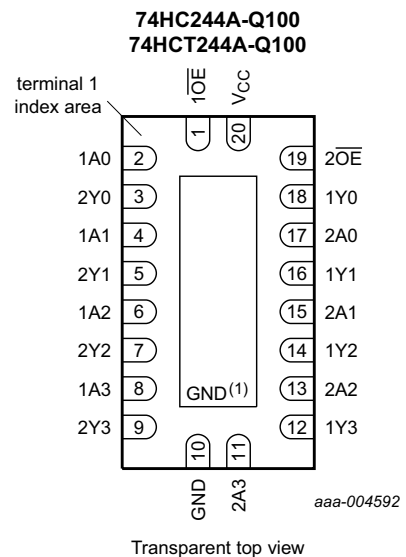


Fig 4. Pin configuration SO20, TSSOP20



(1) This is not a supply pin. The substrate is attached to this pad using conductive die attach material. There is no electrical or mechanical requirement to solder this pad. However, if it is soldered, the solder land should remain floating or be connected to GND.

Fig 5. Pin configuration DHVQFN20

## 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$1\overline{OE}, 2\overline{OE}$	1, 19	output enable input (active LOW)
1A0, 1A1, 1A2, 1A3	2, 4, 6, 8	data input
2Y0, 2Y1, 2Y2, 2Y3	3, 5, 7, 9	bus output
GND	10	ground (0 V)
2A0, 2A1, 2A2, 2A3	17, 15, 13, 11	data input
1Y0, 1Y1, 1Y2, 1Y3	18, 16, 14, 12	bus output
V <sub>CC</sub>	20	supply voltage

## 6. Functional description

Table 3. Function table<sup>[1]</sup>

Input		Output	
nOE	nAn	nYn	
L	L	L	
L	H	H	
H	X	Z	

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7	V
I <sub>IK</sub>	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	-	±20	mA
I <sub>OK</sub>	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	-	±20	mA
I <sub>O</sub>	output current	$-0.5\text{ V} < V_O < V_{CC} + 0.5\text{ V}$	-	±35	mA
I <sub>CC</sub>	supply current		-	70	mA
I <sub>GND</sub>	ground current		-70	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation		[1] -	500	mW

[1] For SO20 packages: above 70 °C, P<sub>tot</sub> derates linearly with 8 mW/K.  
 For TSSOP20 package: above 60 °C, P<sub>tot</sub> derates linearly with 5.5 mW/K.  
 For DHVQFN20 packages: above 60 °C, P<sub>tot</sub> derates linearly with 4.5 mW/K.

## 8. Recommended operating conditions

**Table 5. Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>74HC244-Q100</b>						
$V_{CC}$	supply voltage		2.0	5.0	6.0	V
$V_I$	input voltage		0	-	$V_{CC}$	V
$V_O$	output voltage		0	-	$V_{CC}$	V
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	ns/V
		$V_{CC} = 4.5\text{ V}$	-	1.67	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	ns/V
$T_{amb}$	ambient temperature		-40	-	+125	°C
<b>74HCT244-Q100</b>						
$V_{CC}$	supply voltage		4.5	5.0	5.5	V
$V_I$	input voltage		0	-	$V_{CC}$	V
$V_O$	output voltage		0	-	$V_{CC}$	V
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 4.5\text{ V}$	-	1.67	139	ns/V
$T_{amb}$	ambient temperature		-40	-	+125	°C

## 9. Static characteristics

**Table 6. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74HC244-Q100</b>										
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 2.0\text{ V}$	1.5	1.2	-	1.5	-	1.5	-	V
		$V_{CC} = 4.5\text{ V}$	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0\text{ V}$	4.2	3.2	-	4.2	-	4.2	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 2.0\text{ V}$	-	0.8	0.5	-	0.5	-	0.5	V
		$V_{CC} = 4.5\text{ V}$	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0\text{ V}$	-	2.8	1.8	-	1.8	-	1.8	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$								
		$I_O = -20\ \mu\text{A}; V_{CC} = 2.0\text{ V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20\ \mu\text{A}; V_{CC} = 4.5\text{ V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -20\ \mu\text{A}; V_{CC} = 6.0\text{ V}$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_O = -6.0\text{ mA}; V_{CC} = 4.5\text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
	$I_O = -7.8\text{ mA}; V_{CC} = 6.0\text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V	

**Table 6. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 6.0 mA; V <sub>CC</sub> = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I <sub>O</sub> = 7.8 mA; V <sub>CC</sub> = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I <sub>OZ</sub>	OFF-state output current	per input pin; V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>O</sub> = V <sub>CC</sub> or GND; other inputs at V <sub>CC</sub> or GND; V <sub>CC</sub> = 6.0 V; I <sub>O</sub> = 0 A	-	-	±0.5	-	±5.0	-	±10	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V	-	-	8.0	-	80	-	160	μA
C <sub>I</sub>	input capacitance		-	3.5	-	-	-	-	-	pF
<b>74HCT244-Q100</b>										
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 4.5 V								
		I <sub>O</sub> = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -6 mA	3.98	4.32	-	3.84	-	3.7	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 4.5 V								
		I <sub>O</sub> = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 6.0 mA	-	0.16	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I <sub>OZ</sub>	OFF-state output current	per input pin; V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>O</sub> = V <sub>CC</sub> or GND; other inputs at V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V; I <sub>O</sub> = 0 A	-	-	±0.5	-	±5.0	-	±10	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V; I <sub>O</sub> = 0 A	-	-	8.0	-	80	-	160	μA
ΔI <sub>CC</sub>	additional supply current	per input pin; V <sub>I</sub> = V <sub>CC</sub> - 2.1 V; other inputs at V <sub>CC</sub> or GND; V <sub>CC</sub> = 4.5 V to 5.5 V; I <sub>O</sub> = 0 A	-	70	252	-	315	-	343	μA
C <sub>I</sub>	input capacitance		-	3.5	-	-	-	-	-	pF

## 10. Dynamic characteristics

**Table 7. Dynamic characteristics**

$GND = 0\text{ V}$ ; for load circuit see [Figure 8](#).

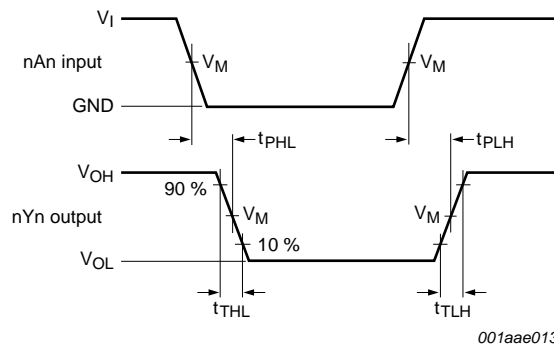
Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Max (85 °C)	Max (125 °C)	
<b>74HC244-Q100</b>								
$t_{pd}$	propagation delay	nAn to nYn; see <a href="#">Figure 6</a> <a href="#">[1]</a>						
		$V_{CC} = 2.0\text{ V}$	-	30	110	145	165	ns
		$V_{CC} = 4.5\text{ V}$	-	11	22	28	33	ns
		$V_{CC} = 5.0\text{ V}; C_L = 15\text{ pF}$	-	9	-	-	-	ns
		$V_{CC} = 6.0\text{ V}$	-	9	19	24	28	ns
$t_{en}$	enable time	nOE to nYn; see <a href="#">Figure 7</a> <a href="#">[2]</a>						
		$V_{CC} = 2.0\text{ V}$	-	36	150	190	225	ns
		$V_{CC} = 4.5\text{ V}$	-	13	30	38	45	ns
		$V_{CC} = 6.0\text{ V}$	-	10	26	33	38	ns
$t_{dis}$	disable time	nOE to nYn or see <a href="#">Figure 7</a> <a href="#">[3]</a>						
		$V_{CC} = 2.0\text{ V}$	-	39	150	190	225	ns
		$V_{CC} = 4.5\text{ V}$	-	14	30	38	45	ns
		$V_{CC} = 6.0\text{ V}$	-	11	26	33	38	ns
$t_t$	transition time	see <a href="#">Figure 6</a> <a href="#">[4]</a>						
		$V_{CC} = 2.0\text{ V}$	-	14	60	75	90	ns
		$V_{CC} = 4.5\text{ V}$	-	5	12	15	18	ns
		$V_{CC} = 6.0\text{ V}$	-	4	10	13	15	ns
$C_{PD}$	power dissipation capacitance	per buffer; $V_I = GND$ to $V_{CC}$ <a href="#">[5]</a>	-	35	-	-	-	pF

**Table 7. Dynamic characteristics ...continued**  
*GND = 0 V; for load circuit see Figure 8.*

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Max (85 °C)	Max (125 °C)	
<b>74HCT244-Q100</b>								
$t_{pd}$	propagation delay	nAn to nYn; see <a href="#">Figure 6</a>	[1]					
		$V_{CC} = 4.5\text{ V}$	-	13	22	28	33	ns
		$V_{CC} = 5.0\text{ V}; C_L = 15\text{ pF}$	-	11	-	-	-	ns
$t_{en}$	enable time	nOE to nYn; $V_{CC} = 4.5\text{ V}$ ; see <a href="#">Figure 7</a>	[2]	15	30	38	45	ns
$t_{dis}$	disable time	nOE to nYn; $V_{CC} = 4.5\text{ V}$ ; see <a href="#">Figure 7</a>	[3]	15	25	31	38	ns
$t_t$	transition time	$V_{CC} = 4.5\text{ V}$ ; see <a href="#">Figure 6</a>	[4]	5	12	15	18	ns
$C_{PD}$	power dissipation capacitance	per buffer; $V_I = \text{GND to } V_{CC} - 1.5\text{ V}$	[5]	35	-	-	-	pF

- [1]  $t_{pd}$  is the same as  $t_{PHL}$  and  $t_{PLH}$ .
- [2]  $t_{en}$  is the same as  $t_{PZH}$  and  $t_{PZL}$ .
- [3]  $t_{dis}$  is the same as  $t_{PHZ}$  and  $t_{PLZ}$ .
- [4]  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .
- [5]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu\text{W}$ ):  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$  where:  
 $f_i$  = input frequency in MHz;  
 $f_o$  = output frequency in MHz;  
 $C_L$  = output load capacitance in pF;  
 $V_{CC}$  = supply voltage in V;  
 $N$  = number of inputs switching;  
 $\sum (C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

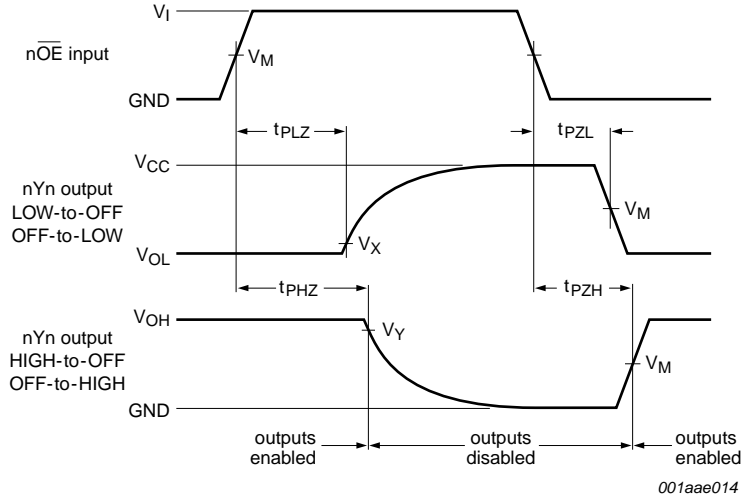
## 11. Waveforms



Measurement points are given in [Table 8](#).  
 $V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

**Fig 6. Input (nAn) to output (nYn) propagation delays and output transition times**



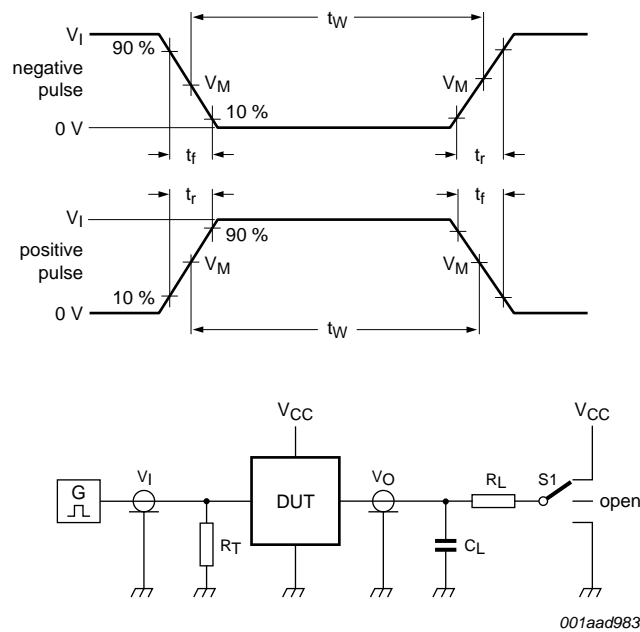


Measurement points are given in [Table 8](#).  
 $V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

**Fig 7. 3-state enable and disable times**

**Table 8. Measurement points**

Type	Input	Output		
	$V_M$	$V_M$	$V_X$	$V_Y$
74HC244-Q100	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$
74HCT244-Q100	1.3 V	1.3 V	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$



Test data is given in [Table 9](#).

Definitions test circuit:

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_L$  = Load resistance.

S1 = Test selection switch.

**Fig 8. Test circuit for measuring switching times**

**Table 9. Test data**

Type	Input		Load		S1 position		
	$V_I$	$t_r, t_f$	$C_L$	$R_L$	$t_{PHL}, t_{PLH}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
74HC244-Q100	$V_{CC}$	6 ns	15 pF, 50 pF	1 k $\Omega$	open	GND	$V_{CC}$
74HCT244-Q100	3 V	6 ns	15 pF, 50 pF	1 k $\Omega$	open	GND	$V_{CC}$

## 12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1



Fig 9. Package outline SOT163-1 (SO20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

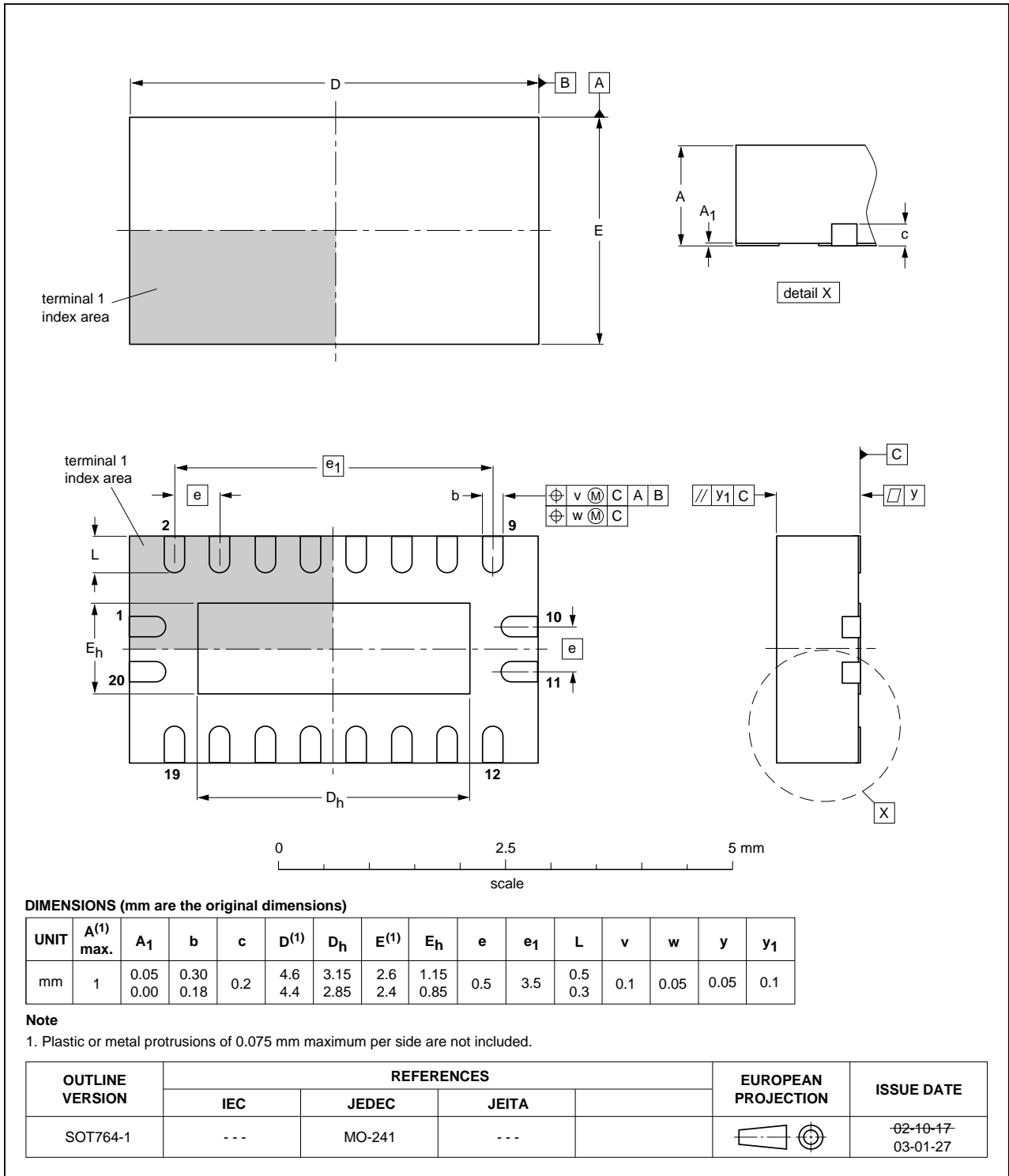
SOT360-1



Fig 10. Package outline SOT360-1 (TSSOP20)

**DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm**

**SOT764-1**



**Fig 11. Package outline SOT764-1 (DHVQFN20)**

## 13. Abbreviations

**Table 10. Abbreviations**

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
MIL	Military

## 14. Revision history

**Table 11. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT244_Q100 v.1	20120807	Product data sheet	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

### 15.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

**Short data sheet** — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

### 15.3 Disclaimers

**Limited warranty and liability** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

**Right to make changes** — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Suitability for use in automotive applications** — This NXP Semiconductors product has been qualified for use in automotive applications. Unless otherwise agreed in writing, the product is not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

**Limiting values** — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

**Terms and conditions of commercial sale** — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

**Translations** — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

## 15.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

## 16. Contact information

---

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)



## 17. Contents

---

<b>1</b>	<b>General description</b> .....	<b>1</b>
<b>2</b>	<b>Features and benefits</b> .....	<b>1</b>
<b>3</b>	<b>Ordering information</b> .....	<b>2</b>
<b>4</b>	<b>Functional diagram</b> .....	<b>2</b>
<b>5</b>	<b>Pinning information</b> .....	<b>3</b>
5.1	Pinning .....	3
5.2	Pin description .....	4
<b>6</b>	<b>Functional description</b> .....	<b>4</b>
<b>7</b>	<b>Limiting values</b> .....	<b>4</b>
<b>8</b>	<b>Recommended operating conditions</b> .....	<b>5</b>
<b>9</b>	<b>Static characteristics</b> .....	<b>5</b>
<b>10</b>	<b>Dynamic characteristics</b> .....	<b>7</b>
<b>11</b>	<b>Waveforms</b> .....	<b>8</b>
<b>12</b>	<b>Package outline</b> .....	<b>11</b>
<b>13</b>	<b>Abbreviations</b> .....	<b>14</b>
<b>14</b>	<b>Revision history</b> .....	<b>14</b>
<b>15</b>	<b>Legal information</b> .....	<b>15</b>
15.1	Data sheet status .....	15
15.2	Definitions .....	15
15.3	Disclaimers .....	15
15.4	Trademarks .....	16
<b>16</b>	<b>Contact information</b> .....	<b>16</b>
<b>17</b>	<b>Contents</b> .....	<b>17</b>

---

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

---

© NXP B.V. 2012.

All rights reserved.

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

Date of release: 7 August 2012

Document identifier: 74HC\_HCT244\_Q100